

Abstract of the Disclosure

Provided is a method of forming quantum dots in which the quantum dots are formed on a thin $\text{In}_x\text{Ga}_{1-x}\text{As}$ strained layer. The $\text{In}(\text{Ga})\text{As}$ quantum dots can be applied to an active layer of an optical device such as a laser diode or an optical
5 detector.